Vishay Siliconix

Automotive P-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	-30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.030				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.052				
I _D (A)	-10.8				
Configuration	Single				

FEATURES

- TrenchFET® power MOSFET
- 100 % R_g and UIS tested
- AEC-Q101 qualified ^c
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

G S
D
P-Channel MOSFET

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	SQ4431EY (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATING	iS (T _C = 25 °C, unless	otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	-30	.,	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C	,	-10.8		
	T _C = 125 °C	l _D	-6.2		
Continuous source current (diode conduction	I _S	-5.4	Α		
Pulsed drain current ^a	I _{DM}	-43.2			
Single pulse avalanche current	1 0411	I _{AS}	-21		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	22	mJ	
Maximum power dissipation ^a	T _C = 25 °C	P _D	6	10/	
	T _C = 125 °C		2	W	
Operating junction and storage temperature	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^b	R_{thJA}	92	°C/W	
Junction-to-foot (drain)		R_{thJF}	25	G/ VV	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR-4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	1	1			·	ı		
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-30	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		-2.0	-2.5	\ \	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = -30 V	-		-1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -30 V, T _J = 125 °C	-		-50	μΑ	
		V _{GS} = 0 V	V _{DS} = -30 V, T _J = 175 °C	-		-150		
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-40	-	-	Α	
		V _{GS} = -4.5 V	I _D = -5 A	-	0.045	0.052	Ω	
Drain activas an atata registance 3	В	V _{GS} = -10 V	I _D = -6 A	-	0.022	0.030		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -6 A, T _J = 125 °C	-	0.027	0.032		
		V _{GS} = -10 V	I _D = -6 A, T _J = 175 °C	-	0.035	0.042		
Forward transconductance b	9 _{fs}	V _{DS} = -15 V, I _D = -6 A		-	25	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	1010	1265	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = -15 \text{ V}, f = 1 \text{ MHz}$	-	243	-		
Reverse transfer capacitance	C _{rss}	7		-	167	-		
Total gate charge ^c	Qg			-	25	-		
Gate-source charge c	Q_{gs}	V _{GS} = -10 V	$V_{DS} = -15 \text{ V}, I_{D} = -7.2 \text{ A}$	-	4	-	nC	
Gate-drain charge ^c	Q_{gd}			-	5	-		
Gate resistance	R_g	f = 1 MHz		1.5	3.36	5.5	Ω	
Turn-on delay time ^c	t _{d(on)}				10	-		
Rise time ^c	t _r	V_{DD} = -15 V, R_L = 15 Ω $I_D \cong$ -1 A, V_{GEN} = -10 V, R_g = 6 Ω		-	12	-	ns	
Turn-off delay time ^c	t _{d(off)}			-	33	-		
Fall time ^c	t _f			-	15	-		
Source-Drain Diode Ratings and Char	racteristics ^b	•						
Pulsed current ^a	I _{SM}			-	-40	-	Α	
Forward voltage	V _{SD}	$I_F = -2.1 \text{ A}, V_{GS} = 0$		-	-0.8	-1.1	V	

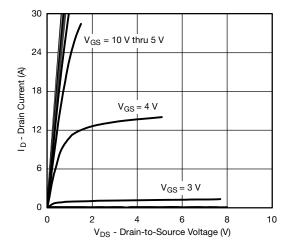
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

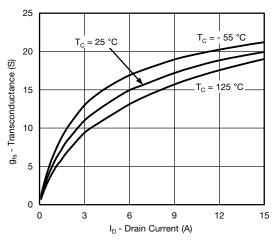
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



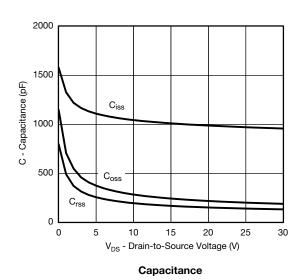
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

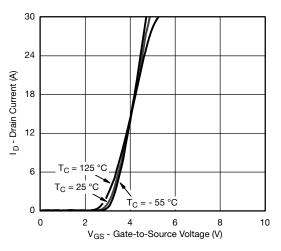


Output Characteristics

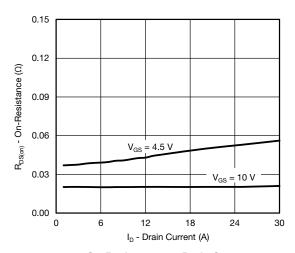


Transconductance

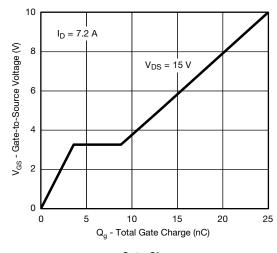




Transfer Characteristics

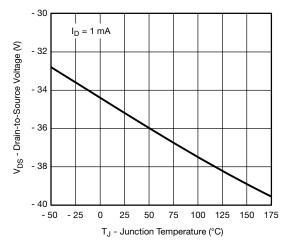


On-Resistance vs. Drain Current

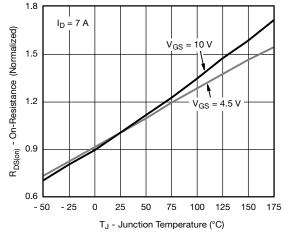




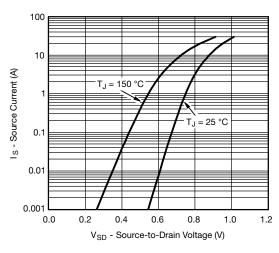
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



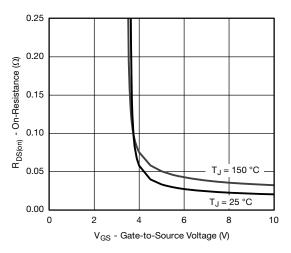
On-Resistance vs. Junction Temperature



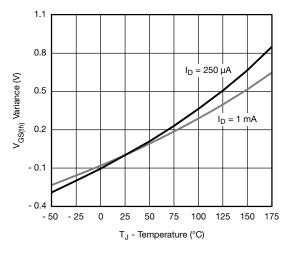
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

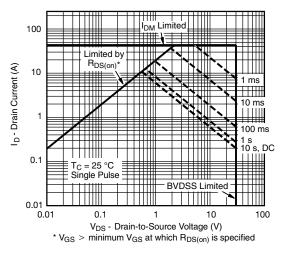


Threshold Voltage

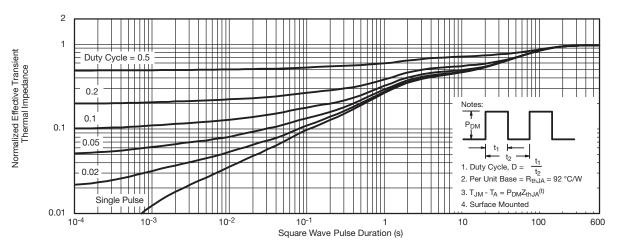
For technical questions, contact: automostechsu



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



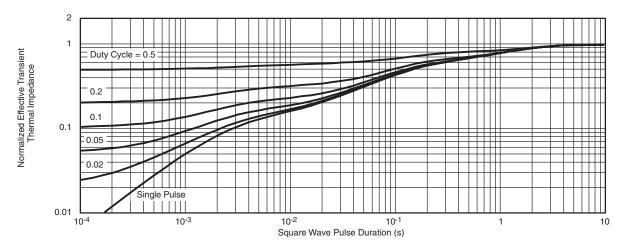
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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